



Introduction & Motivation

Motivation: Understand and measure thermopower in a P-doped quantum material.



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Device Layer (Si)
≈ 250 nm

The Handle (Si)
≈ 750 μm → ≈ 200 μm

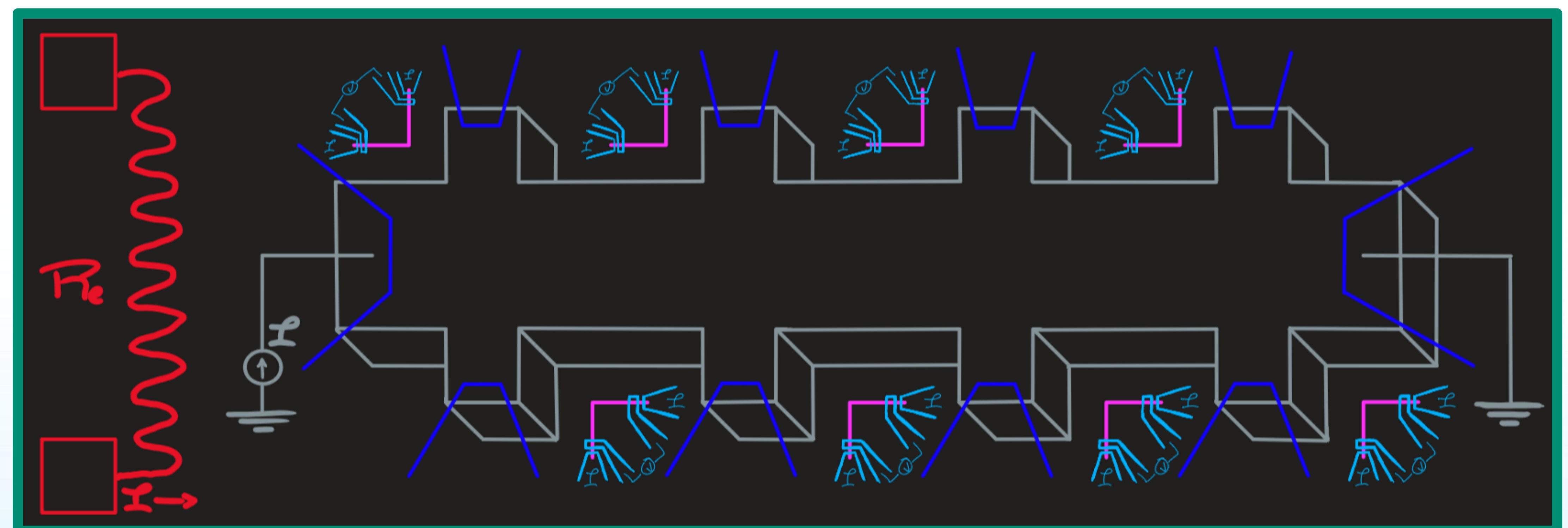
P-Doped δ Layer

"BOX" Layer (SiO₂)
≈ 200 nm

Measurements of Interest:

- Carrier Type, Density, and Mobility
- Seebeck Coefficient

Hall Bar with a Heater and a ton of Thermometers



The Seebeck Coefficient

$$S = \frac{\partial V}{\partial T} = - \frac{\Delta V}{\Delta T}$$



Introduction & Motivation Continued

Why SOI?

Thermal Ohm's Law

$$\Delta T = R_{th} \dot{Q}$$

Where $R_{th} = L/kA = L/kwt$

$$\Rightarrow R_{th, Si} = \frac{10\mu m}{\left(10 \frac{W}{m \cdot K}\right)(500\mu m)(10\mu m)} = 200 K/W$$

Therefore, to achieve a temperature difference of 1 K we will need

$$\Rightarrow \dot{Q}_{Si} = \Delta T / R_{th, Si} = \frac{1K}{200 \frac{K}{W}} = 5mW$$

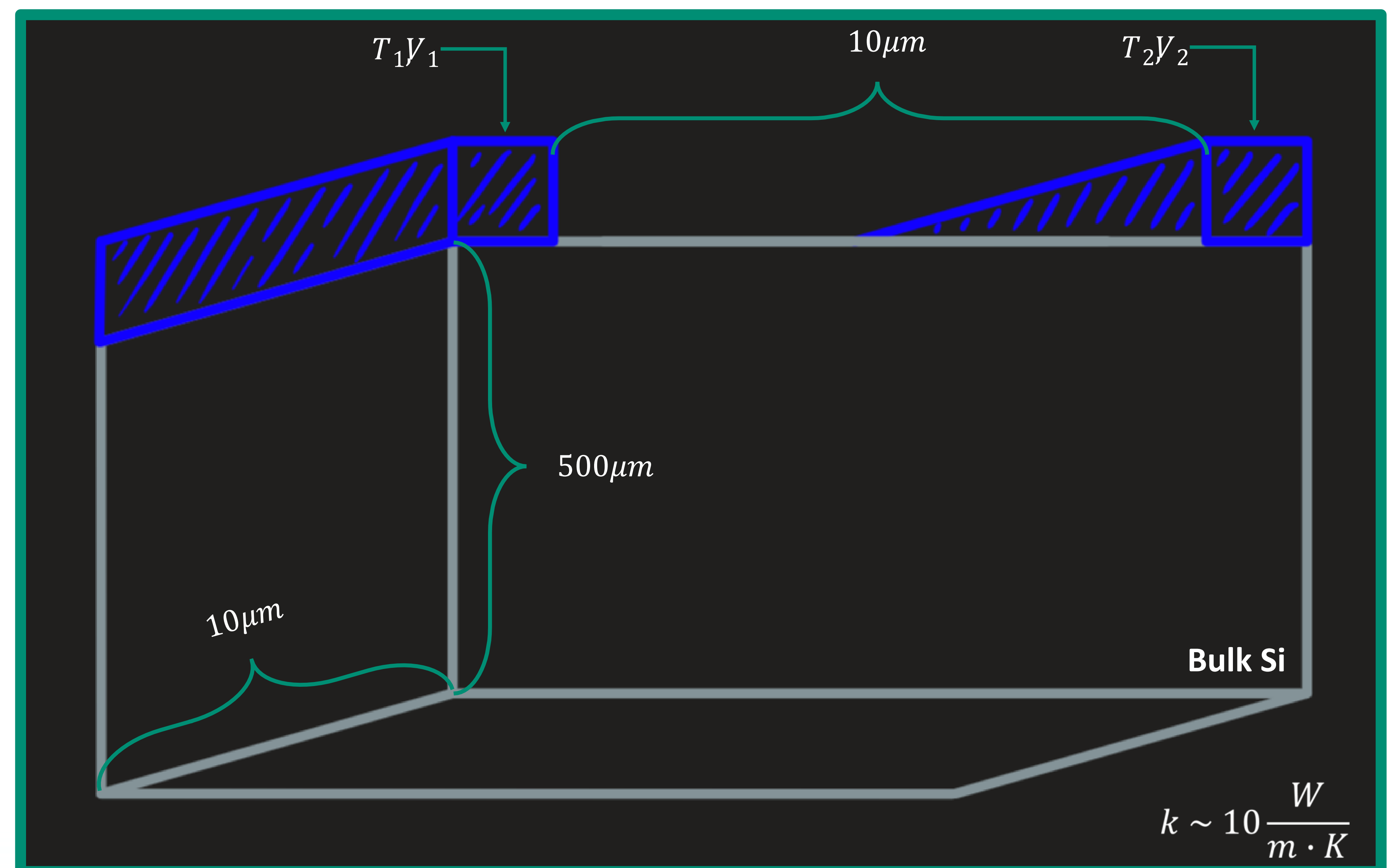
Cryogenic System Power Output Limits:

- ➔ 3He can produce $40\mu W$ of cooling power
- ➔ Dilution Fridge can produce between $200\mu W$ and $400\mu W$ of cooling power

& if we compare

$$t_{Si} = 500\mu m \text{ vs. } t_{SOI} = 250nm$$

Nominal Dimensions for Optical Lithography Patterning



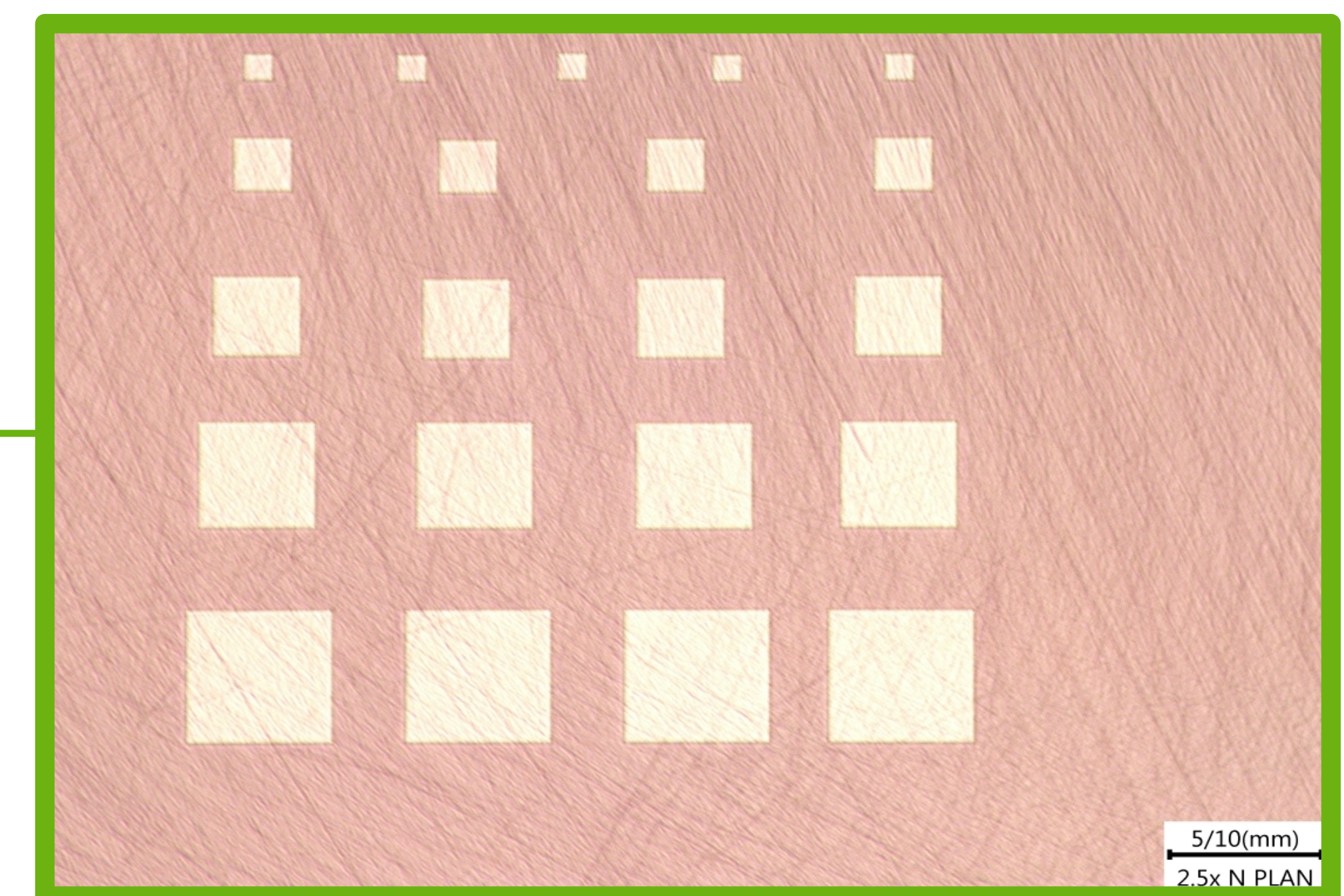
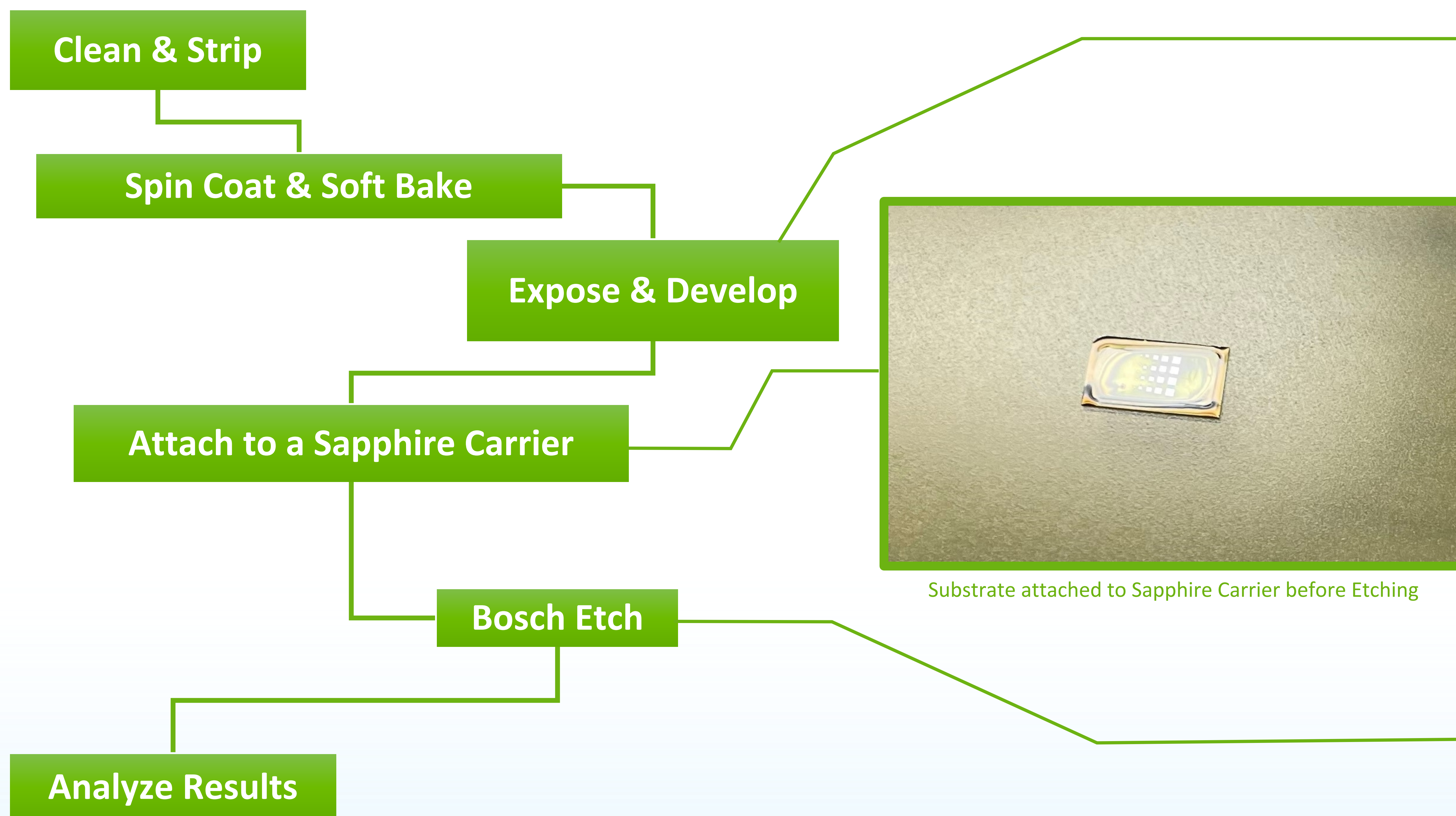
$$\Rightarrow \dot{Q}_{SOI} = 2.5\mu W \text{ (2000 times less!!)}$$



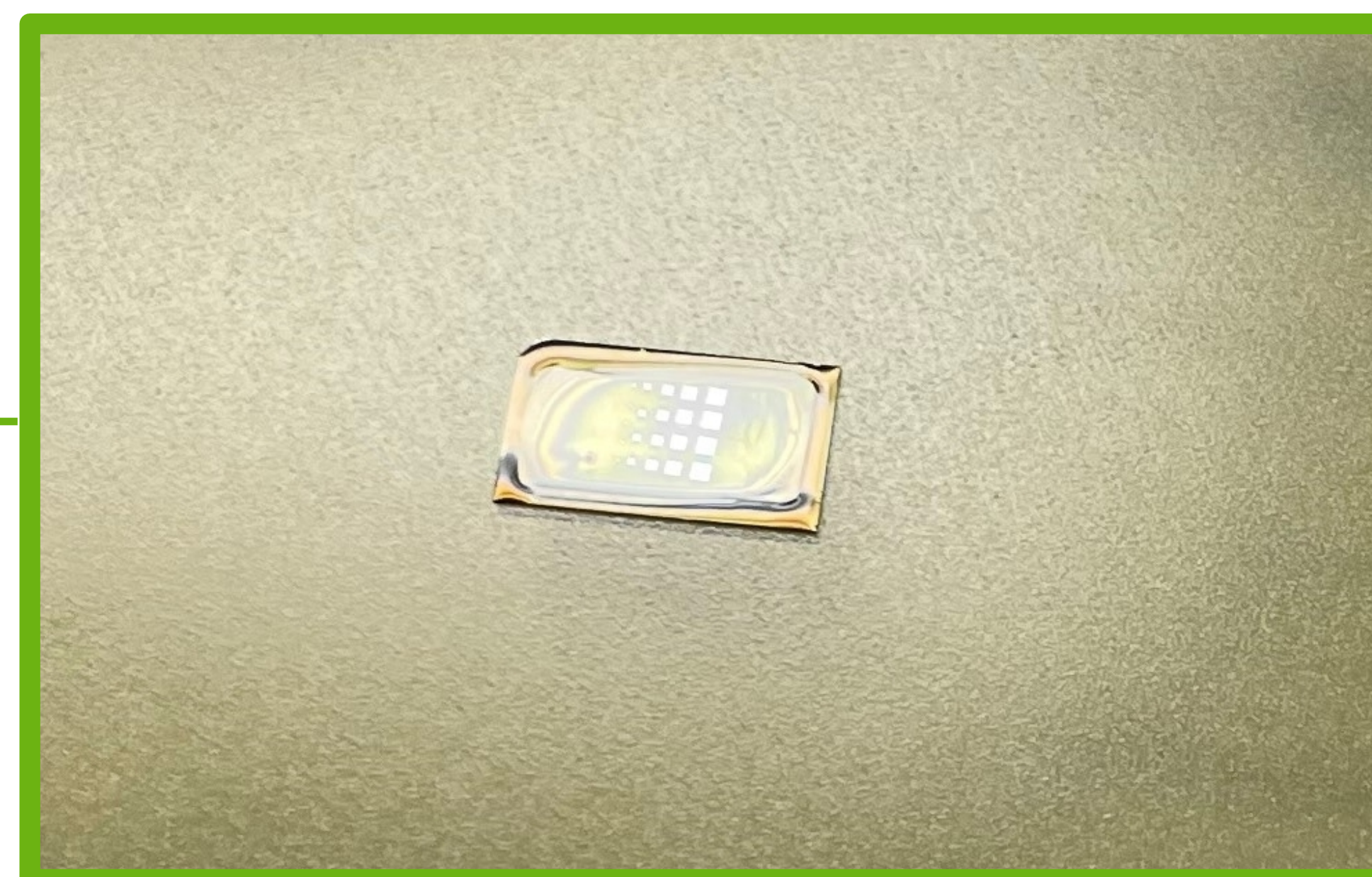
Approach

QUESTION: How big of a membrane can we make?

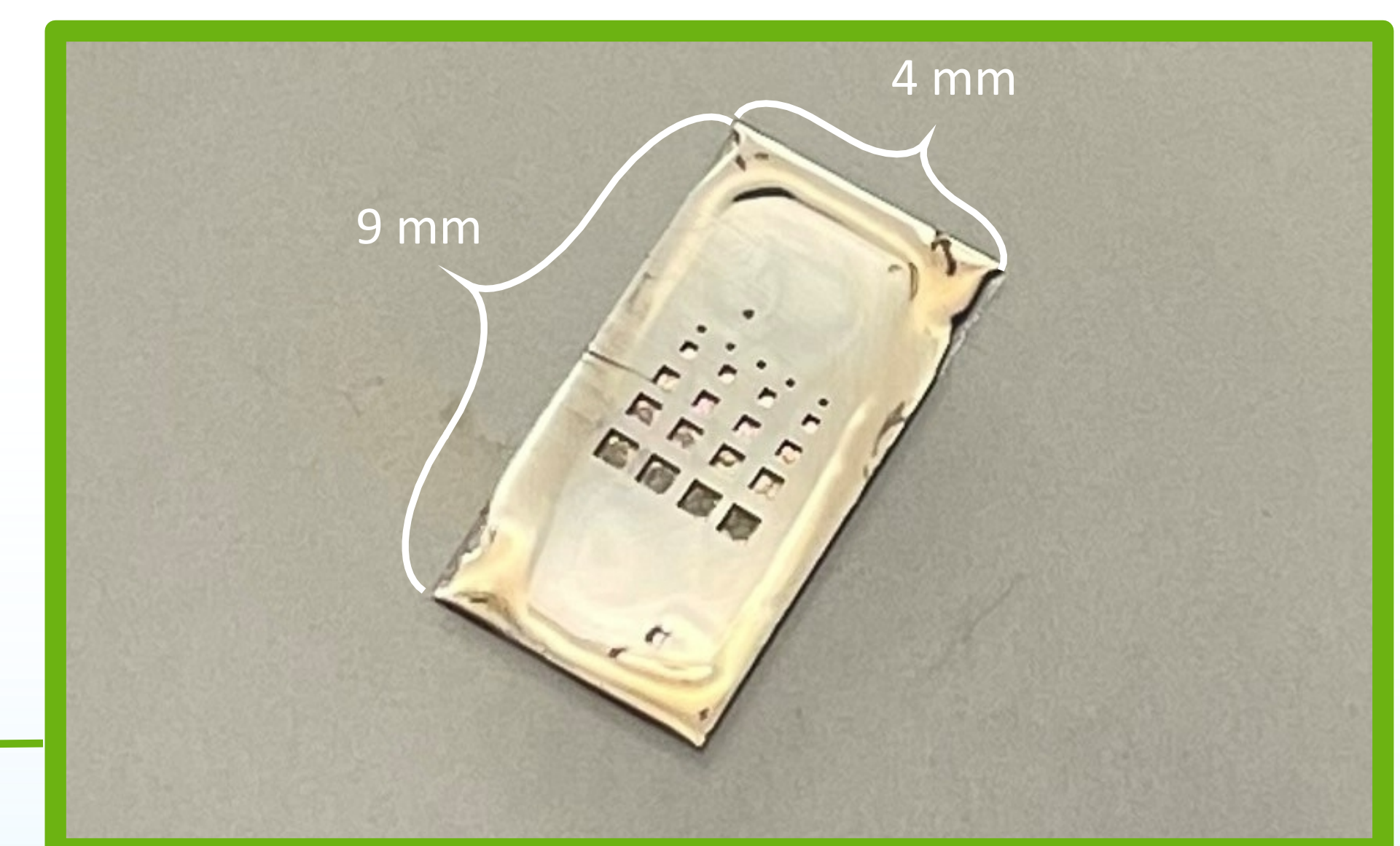
My Process Flow



Developed Pattern on the Handle prior to sub mounting



Substrate attached to Sapphire Carrier before Etching

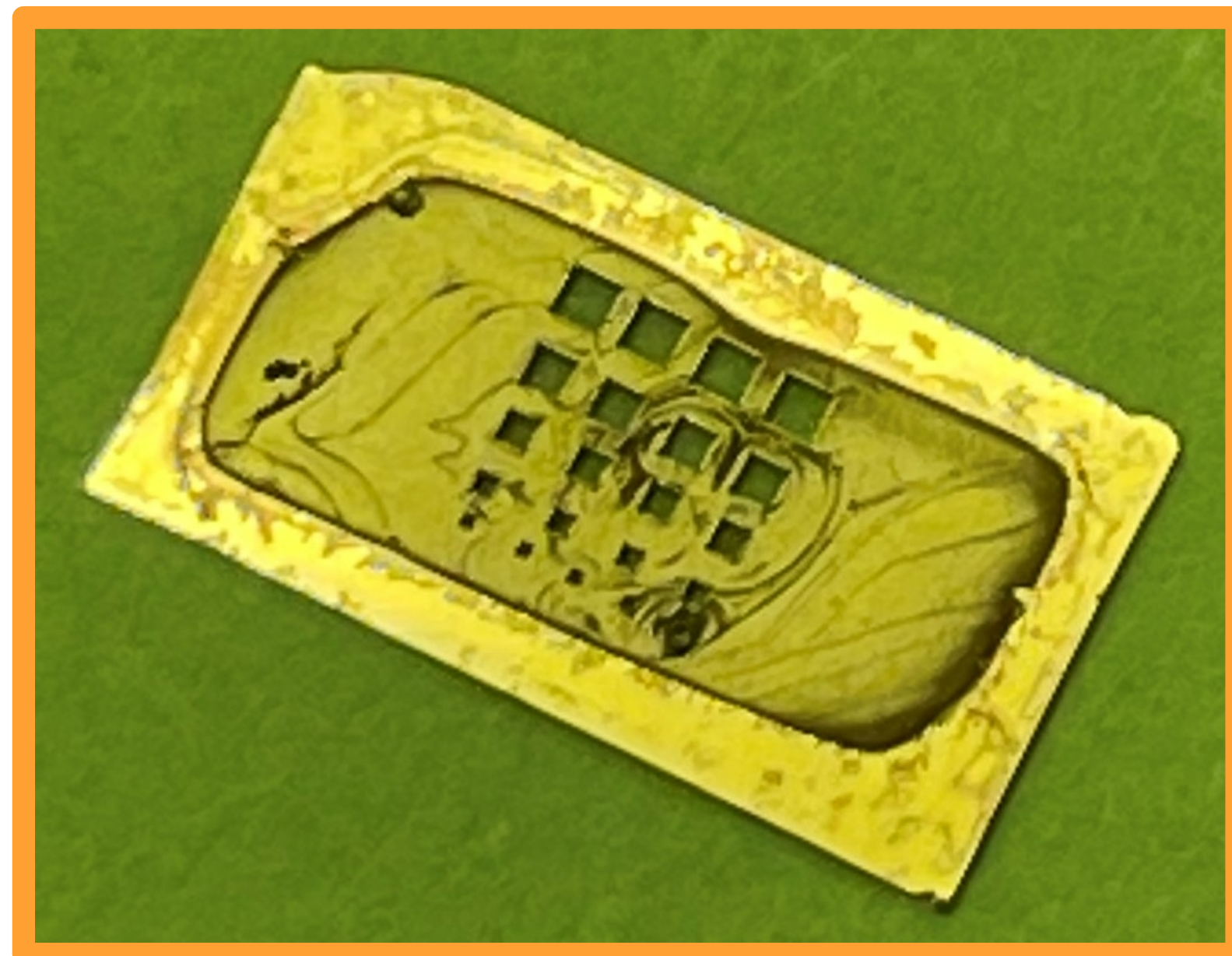


Substrate attached to Sapphire Carrier after Etching



Challenges

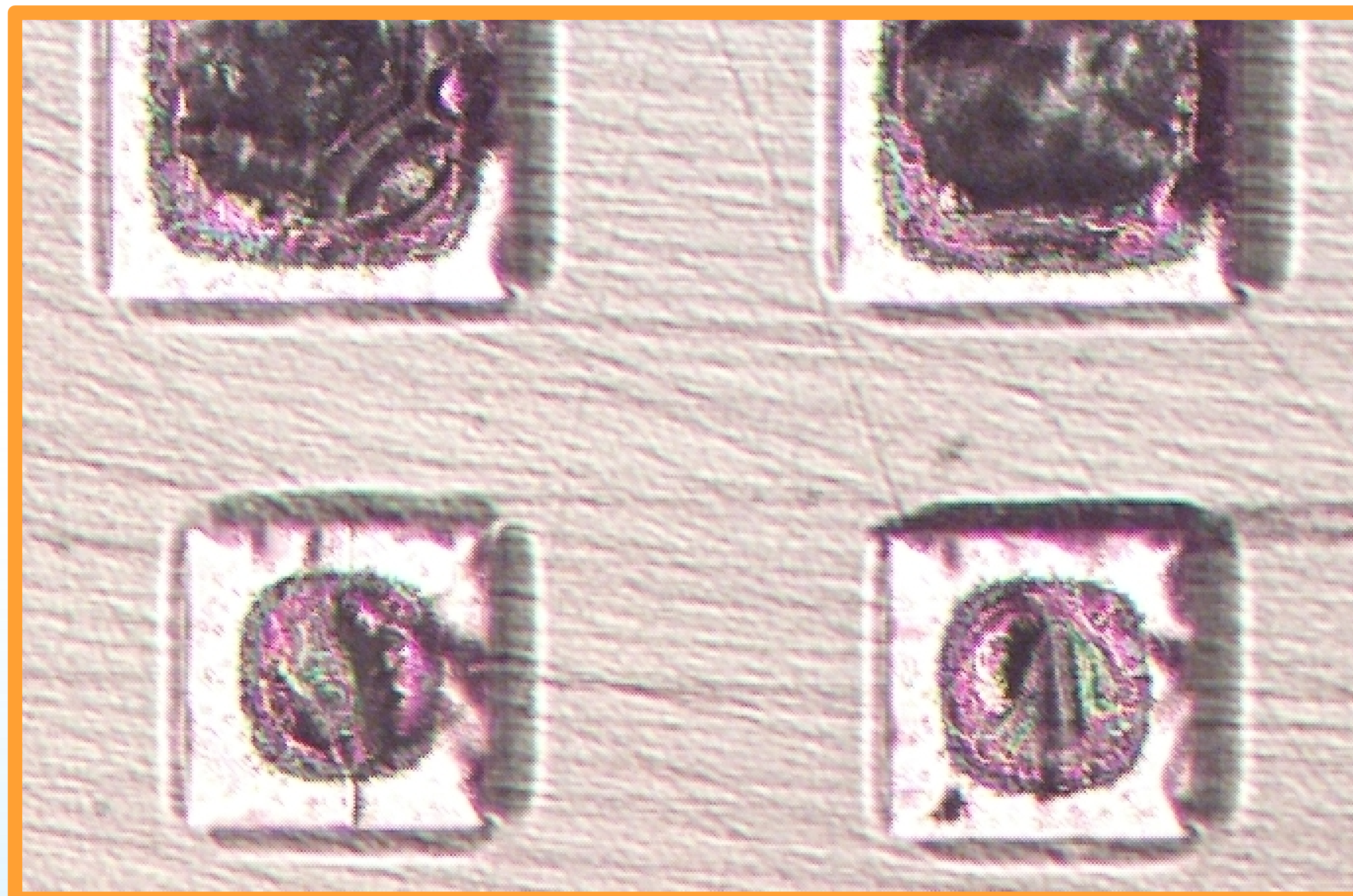
1.) Depleted Resist & Blown Out Membranes



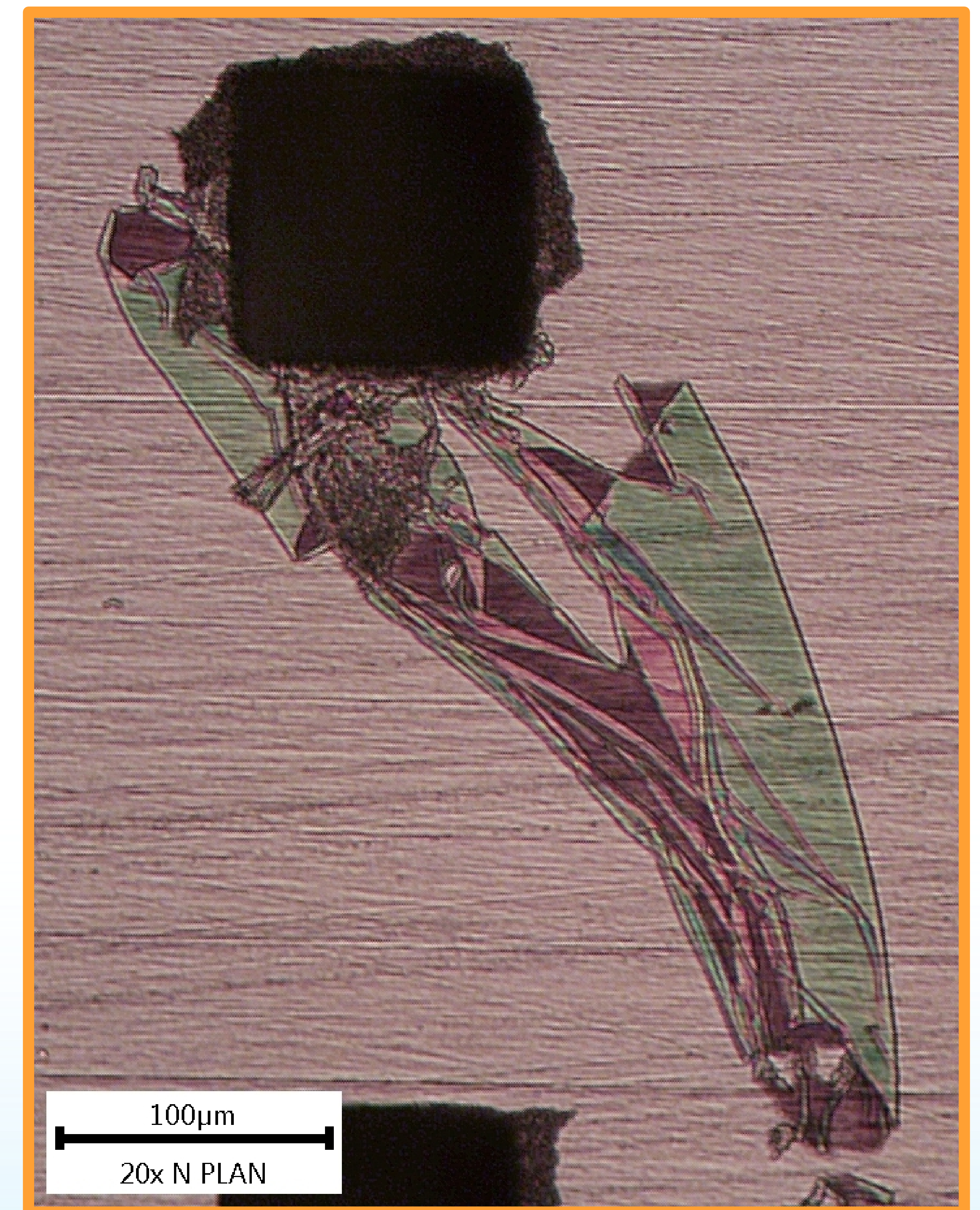
Our Response:

- 1) Thicker Resist & Si Etch Rate Test
- 2) Bosch Etch with a 2 Phase Process
- 3) Add Protective Coating to the Device Layer, such as ProTEK B3

2.) Directional Control Issue



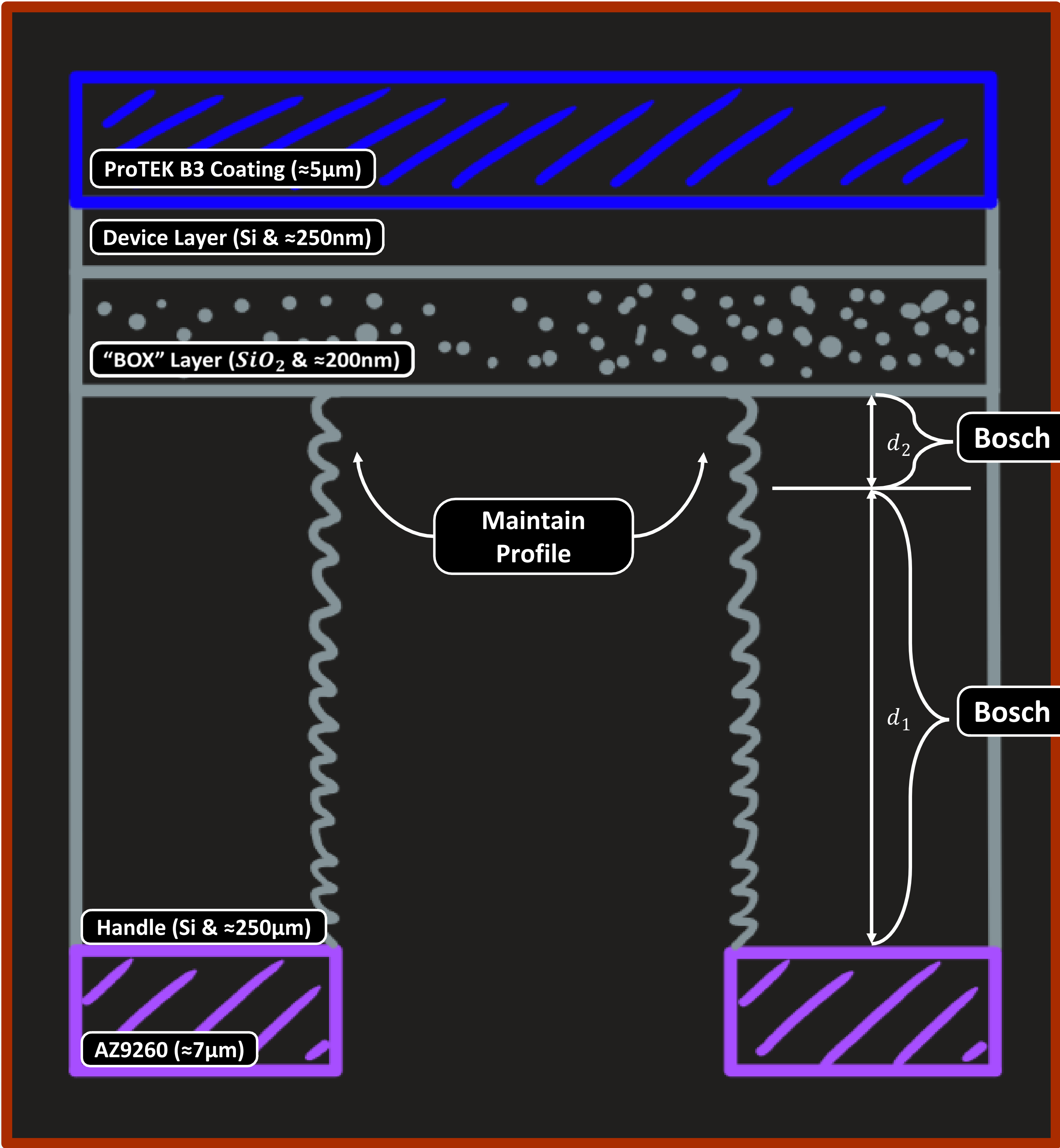
3.) Mechanical Failure Evidence



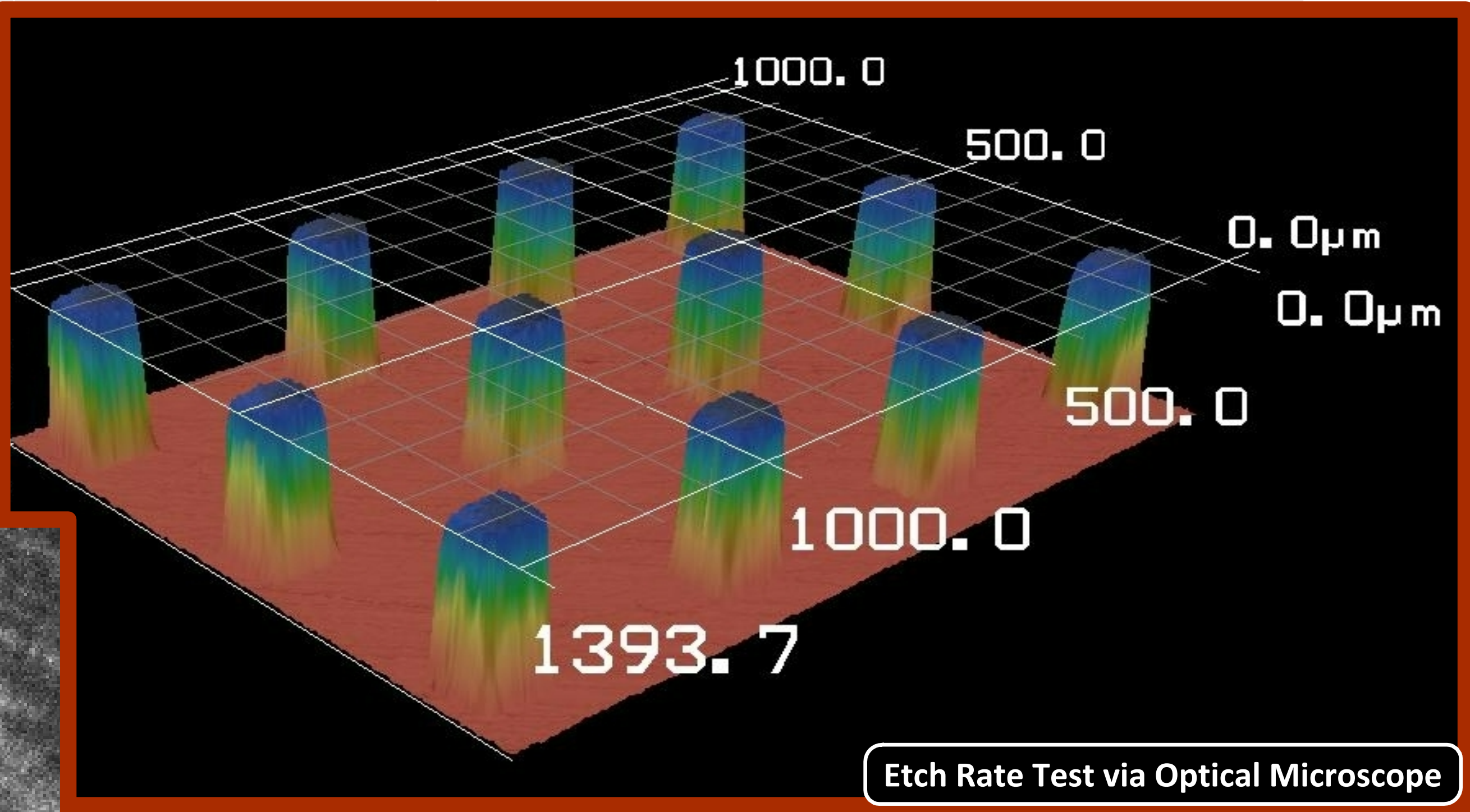
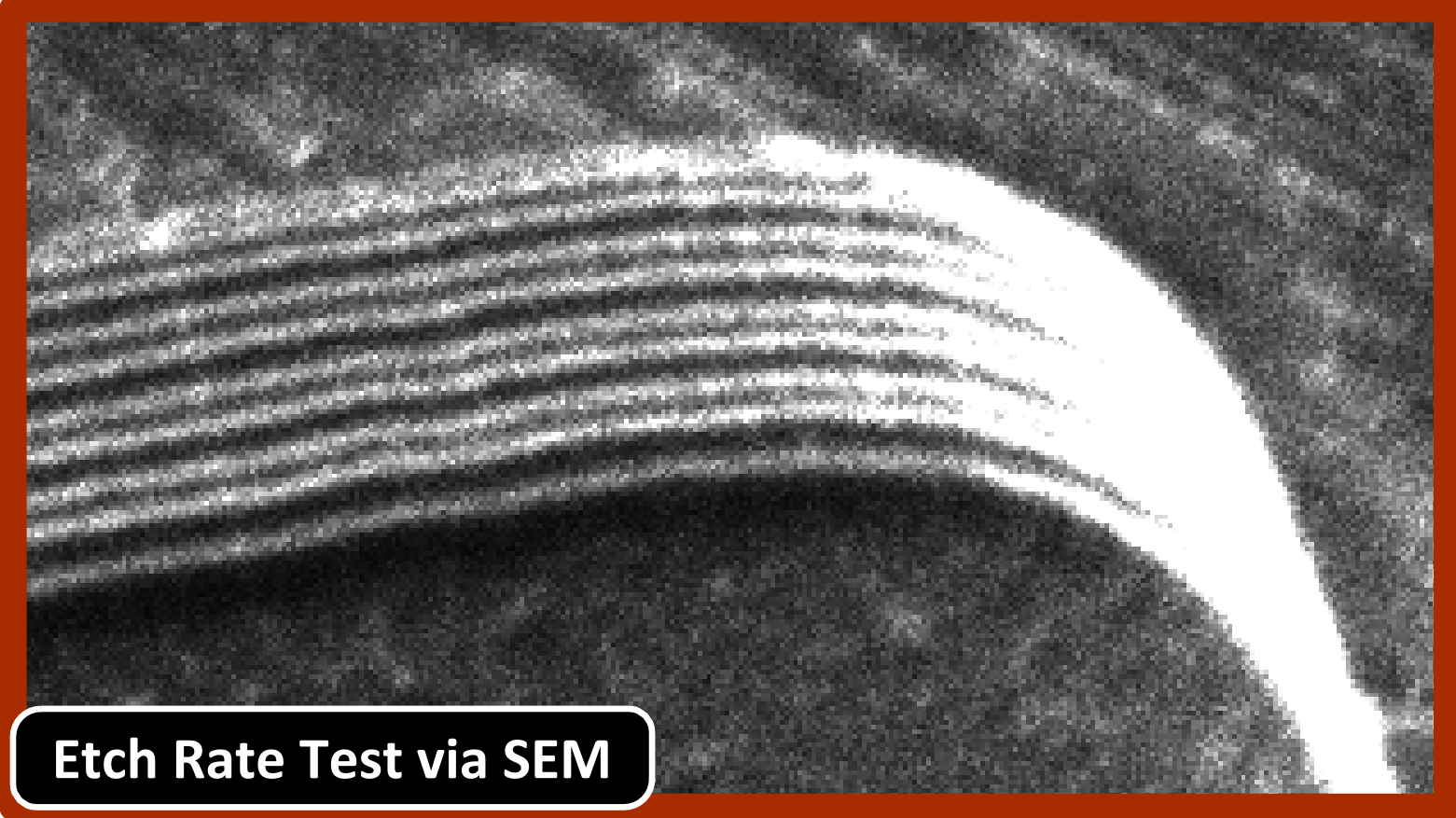


Results

Quantified Etch Rates & Developed Lithography and Etching Recipes

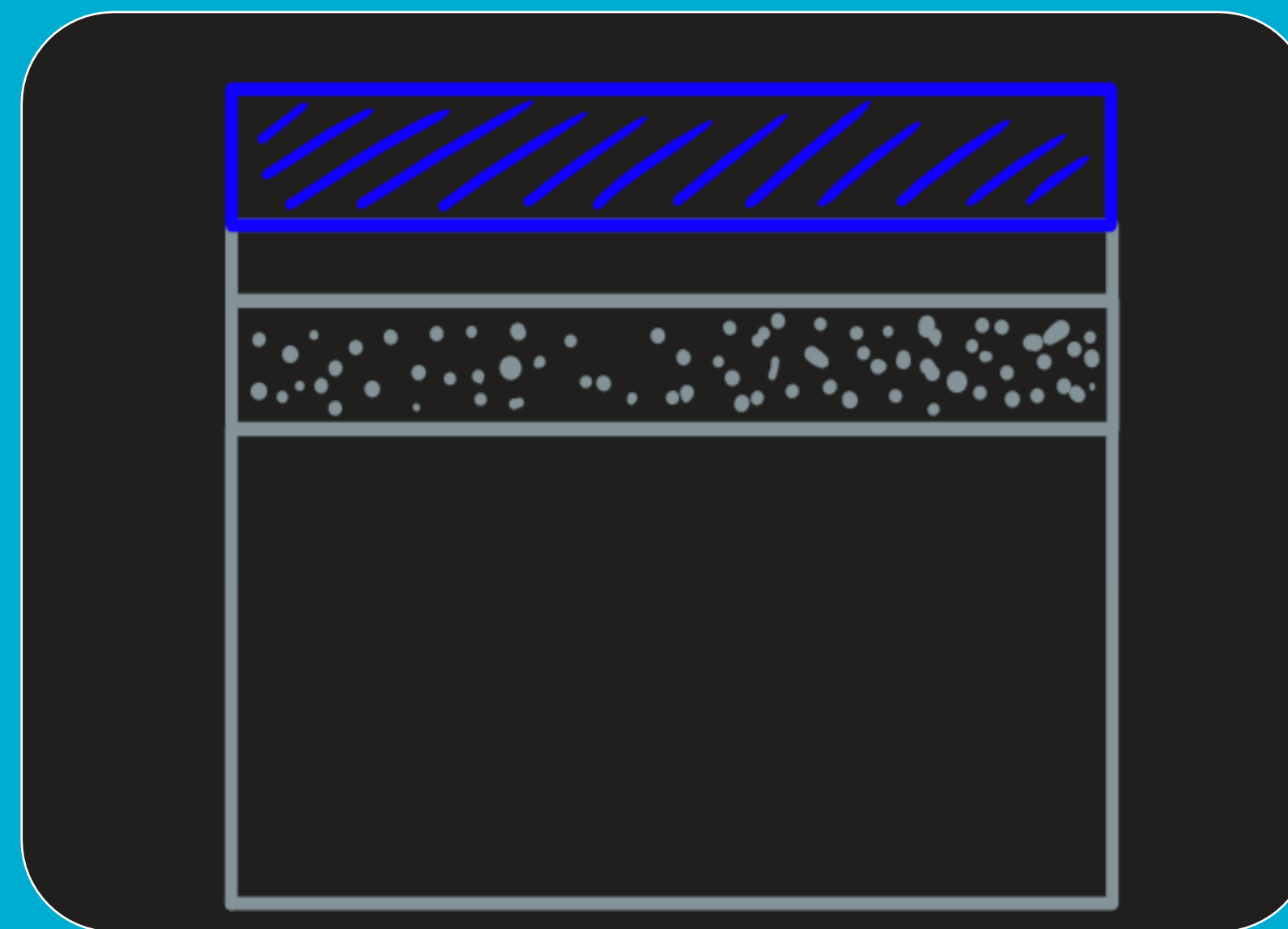


Test	Phase	Material	Etch Rate
#2	#1	Si	$\sim 0.604 \frac{\mu\text{m}}{\text{cycle}}$
#6	#1	SiO_2	$\sim 4.3 \frac{\text{nm}}{\text{cycle}}$
#6	#1	AZ9260	$\sim 15 \frac{\text{nm}}{\text{cycle}}$
#7	#1	Si	$\sim 0.623 \frac{\mu\text{m}}{\text{cycle}}$
#11	#2	Si	$\sim 0.762 \frac{\mu\text{m}}{\text{cycle}}$
#13	#2		



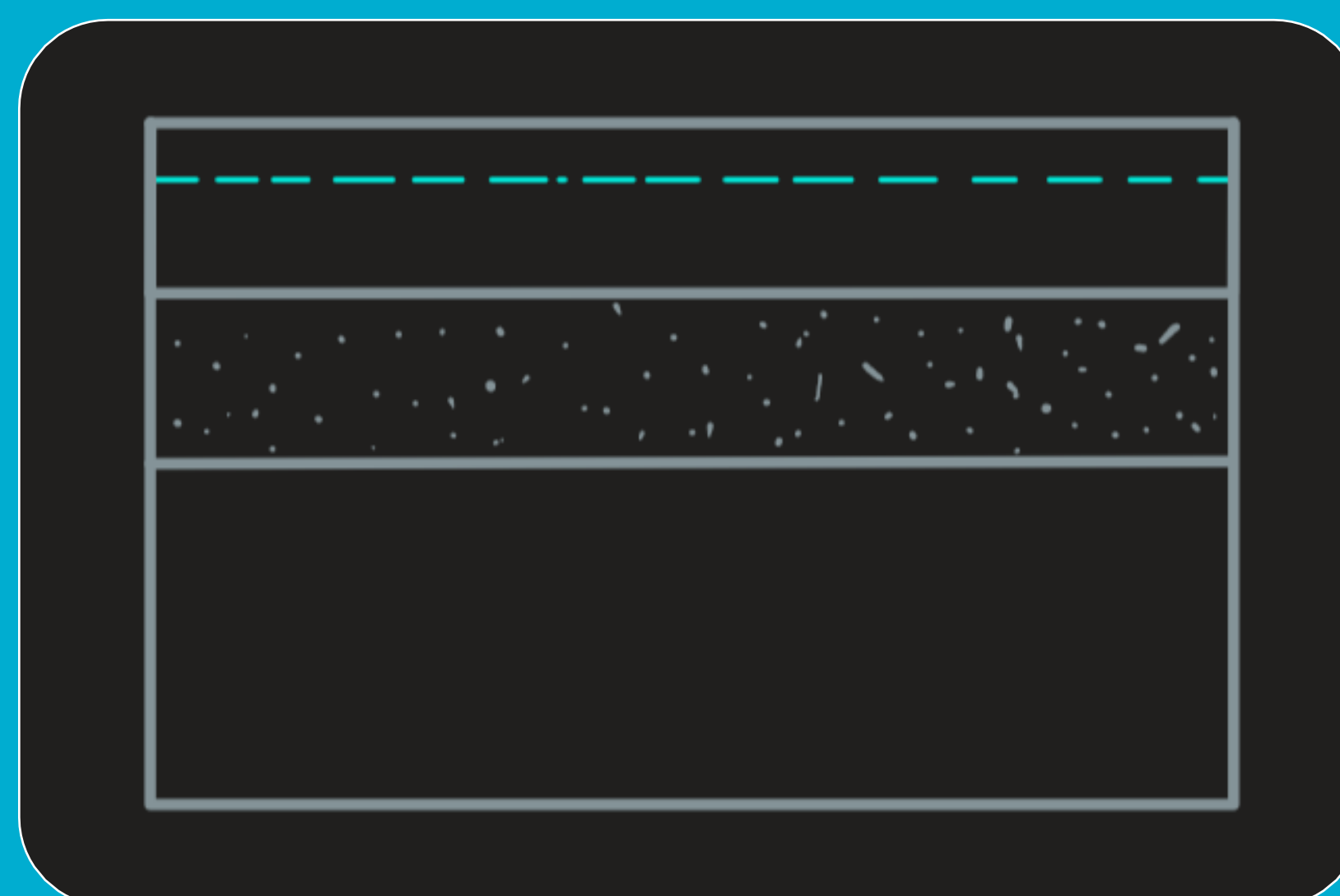


Ongoing & Future Work



Using a Polymer as Structural Support

- Spin coat the device layer before spin resist on the handle.
- For Example, a ProTEK B3 Coating is used to protect delicate front-side circuitry during back-side micromachining.



Use an SOI with a thicker BOX and Device

- Pro: Increases the structural integrity
- Con: New process needed for embedding Phosphine